

MA4S159

Silicon epitaxial planar type

For switching circuits

■ Features

- Small S-mini type 4-pin package
- Two isolated elements contained in one package, allowing high-density mounting
- Flat lead type, resulting in improved mounting efficiency and solderability with the high-speed mounting machine
- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	80	V
Peak reverse voltage	V_{RM}	80	V
Average forward current	Single	$I_{F(AV)}$	100
	Double		75
Peak forward current	Single	I_{FM}	225
	Double		170
Non-repetitive peak forward surge current*	Single	I_{FSM}	500
	Double		375
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

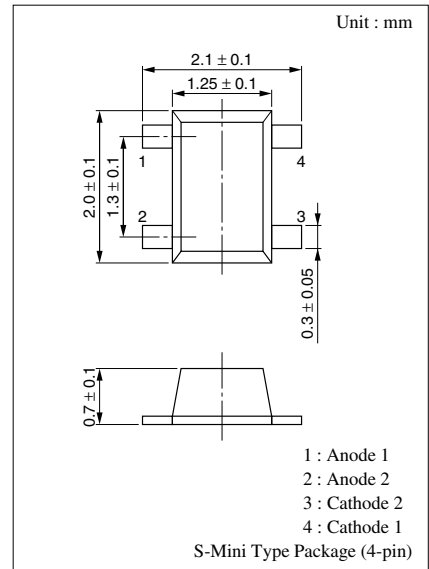
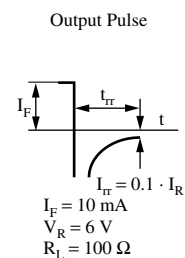
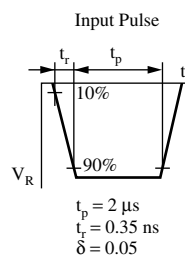
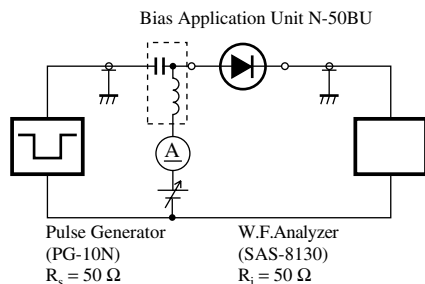
Note) * : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 75 \text{ V}$			0.1	μA
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$		0.95	1.2	V
Reverse voltage (DC)	V_R	$I_R = 100 \mu\text{A}$	80			V
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$		0.9	2	pF
Reverse recovery time*	t_{rr}	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}$ $I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$			3	ns

Note) 1. Rated input/output frequency: 100 MHz

2. * : t_{rr} measuring circuit



Marking Symbol: M1B

Internal Connection

